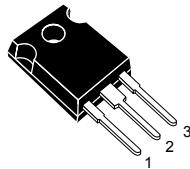
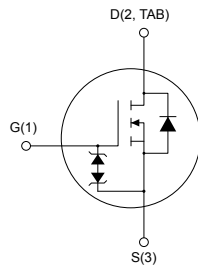


N-channel 600 V, 35 mΩ typ., 63 A MDmesh™ M6 Power MOSFET in a TO-247 package


TO-247


AM01479V1



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STW68N60M6	600 V	41 mΩ	63 A

- Reduced switching losses
- Lower R_{DS(on)} per area vs previous generation
- Low gate input resistance
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications
- LLC converters
- Boost PFC converters

Description

The new MDmesh™ M6 technology incorporates the most recent advancements to the well-known and consolidated MDmesh family of SJ MOSFETs. STMicroelectronics builds on the previous generation of MDmesh devices through its new M6 technology, which combines excellent R_{DS(on)} per area improvement with one of the most effective switching behaviors available, as well as a user-friendly experience for maximum end-application efficiency.

Maturity status link

[STW68N60M6](#)

Device summary

Order code	STW68N60M6
Marking	68N60M6
Package	TO-247
Packing	Tube

1 Electrical ratings

Table 1. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 25	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	63	A
	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	40	A
$I_{DM}^{(1)}$	Drain current (pulsed)	252	A
P_{TOT}	Total power dissipation at $T_C = 25\text{ }^\circ\text{C}$	390	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	15	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	100	
T_{stg}	Storage temperature range	-55 to 150	$^\circ\text{C}$
T_j	Operating junction temperature range		

1. Pulse width is limited by safe operating area.
2. $I_{SD} \leq 63\text{ A}$, $di/dt \leq 400\text{ A}/\mu\text{s}$, $V_{DS(peak)} < V_{(BR)DSS}$, $V_{DD} = 400\text{ V}$
3. $V_{DS} \leq 480\text{ V}$

Table 2. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.32	$^\circ\text{C}/\text{W}$
$R_{thj-amb}$	Thermal resistance junction-ambient	50	$^\circ\text{C}/\text{W}$

Table 3. Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	7.5	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	1100	mJ

2 Electrical characteristics

($T_C = 25\text{ °C}$ unless otherwise specified)

Table 4. On /off-states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}, I_D = 1\text{ mA}$	600			V
I_{DSS}	Zero-gate voltage drain current	$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}, V_{DS} = 600\text{ V}, T_C = 125\text{ °C}^{(1)}$			100	
I_{GSS}	Gate-body leakage current	$V_{DS} = 0\text{ V}, V_{GS} = \pm 25\text{ V}$			± 5	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 250\text{ }\mu\text{A}$	3.25	4	4.75	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}, I_D = 31.5\text{ A}$		35	41	$\text{m}\Omega$

1. Defined by design, not subject to production test.

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 100\text{ V}, f = 1\text{ MHz}$	-	4360	-	pF
C_{oss}	Output capacitance		-	235	-	pF
C_{rss}	Reverse transfer capacitance		-	13	-	pF
$C_{oss\text{ eq.}}^{(1)}$	Equivalent output capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 0\text{ to }480\text{ V}$	-	713	-	pF
R_G	Intrinsic gate resistance	$f = 1\text{ MHz}$ open drain	-	1.6	-	Ω
Q_g	Total gate charge	$V_{DD} = 480\text{ V}, I_D = 63\text{ A},$ $V_{GS} = 0\text{ to }10\text{ V}$ (see Figure 14. Test circuit for gate charge behavior)	-	106	-	nC
Q_{gs}	Gate-source charge		-	29	-	nC
Q_{gd}	Gate-drain charge		-	51	-	nC

1. $C_{oss\text{ eq.}}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS} .

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 300\text{ V}, I_D = 30\text{ A},$ $R_G = 4.7\text{ }\Omega, V_{GS} = 10\text{ V}$ (see Figure 13. Test circuit for resistive load switching times and Figure 18. Switching time waveform)	-	42	-	ns
t_r	Rise time		-	28	-	ns
$t_{d(off)}$	Turn-off delay time		-	130	-	ns
t_f	Fall time		-	8	-	ns

Table 7. Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		63	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		252	A
$V_{SD}^{(2)}$	Forward on voltage	$V_{GS} = 0\text{ V}$, $I_{SD} = 63\text{ A}$	-		1.6	V
t_{rr}	Reverse recovery time	$I_{SD} = 63\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,	-	308		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 60\text{ V}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	4.3		μC
I_{RRM}	Reverse recovery current		-	26		A
t_{rr}	Reverse recovery time	$I_{SD} = 63\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$,	-	504		ns
Q_{rr}	Reverse recovery charge	$V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 15. Test circuit for inductive load switching and diode recovery times)	-	10.8		μC
I_{RRM}	Reverse recovery current		-	38		A

1. Pulse width is limited by safe operating area.
2. Pulse test: pulse duration = 300 μs , duty cycle 1.5%.

2.1 Electrical characteristics (curves)

Figure 1. Safe operating area

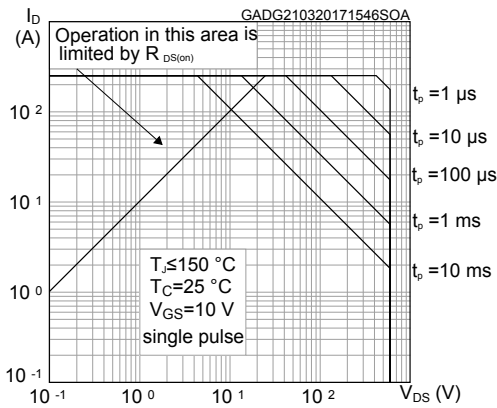


Figure 2. Thermal impedance

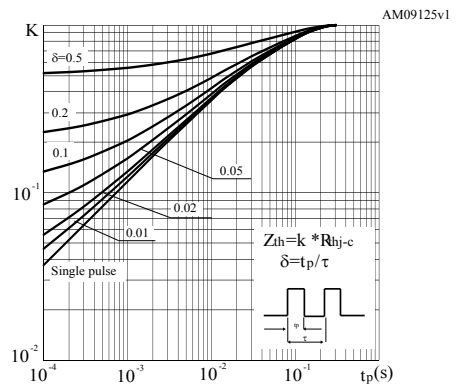


Figure 3. Output characteristics

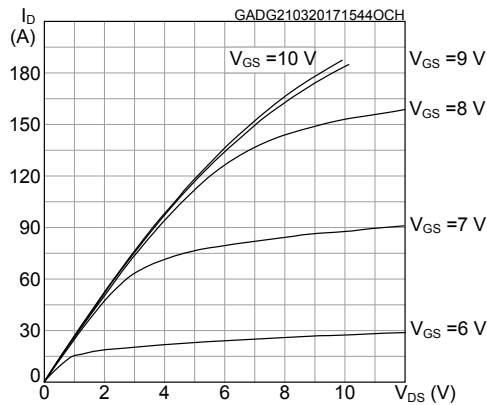


Figure 4. Transfer characteristics

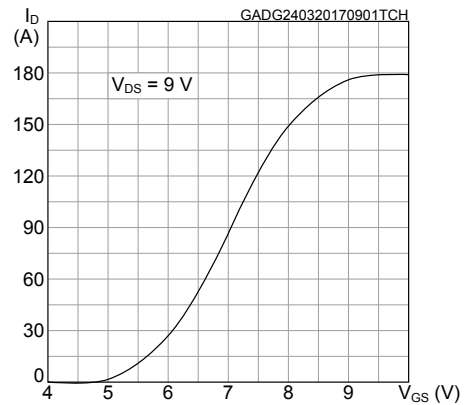


Figure 5. Gate charge vs gate-source voltage

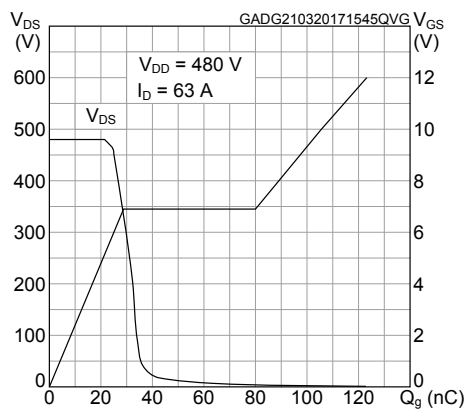


Figure 6. Static drain-source on-resistance

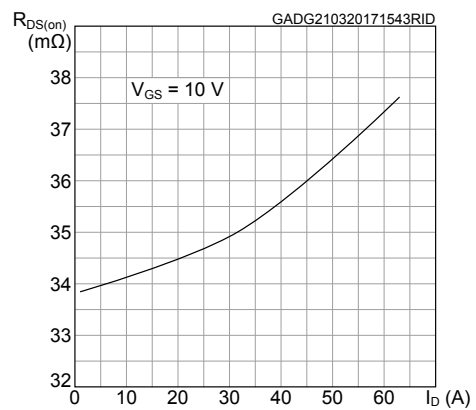


Figure 7. Capacitance variations

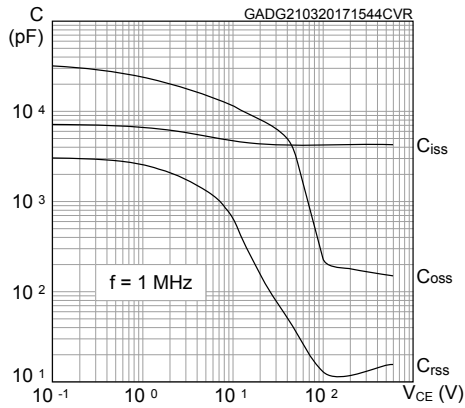


Figure 8. Normalized gate threshold vs. temperature

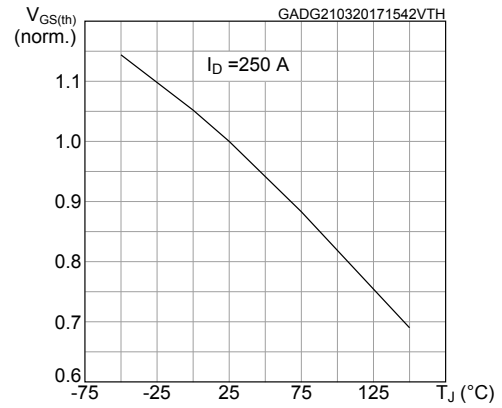


Figure 9. Normalized on-resistance vs. temperature

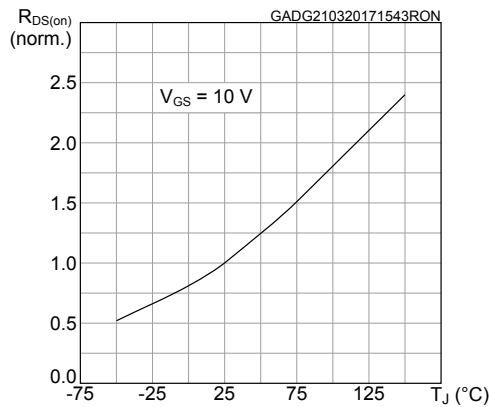


Figure 10. Normalized $V_{(BR)DSS}$ vs. temperature

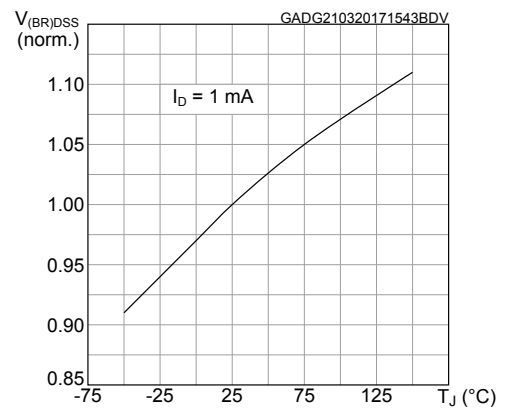


Figure 11. Output capacitance stored energy

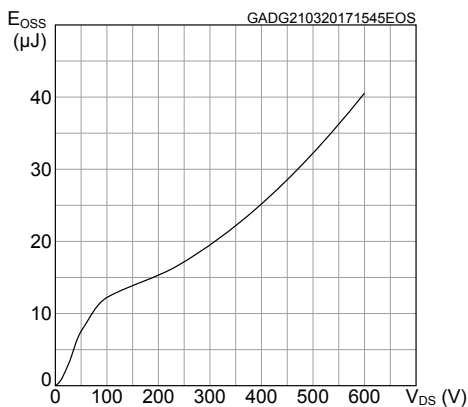
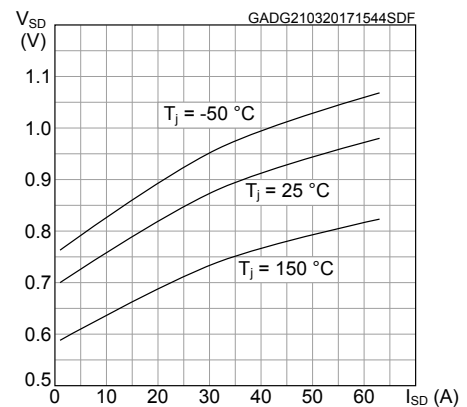


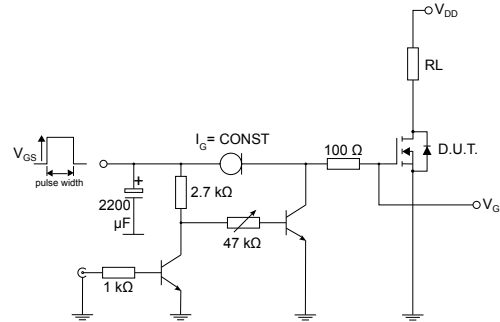
Figure 12. Source-drain diode forward characteristics



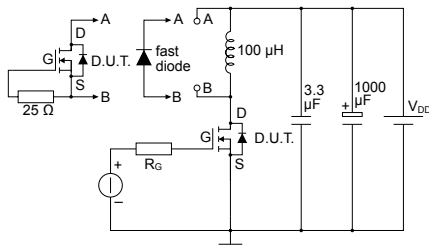
3 Test circuits

Figure 13. Test circuit for resistive load switching times

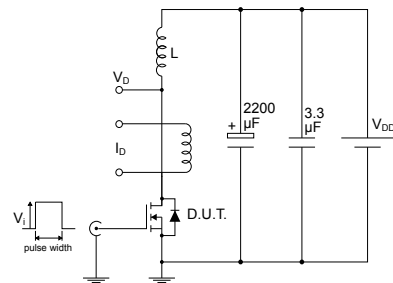

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Figure 14. Test circuit for gate charge behavior


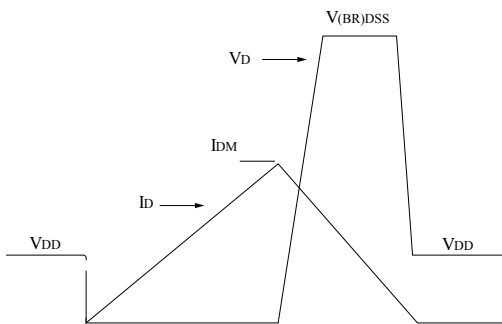
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Figure 15. Test circuit for inductive load switching and diode recovery times


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Figure 16. Unclamped inductive load test circuit


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Figure 17. Unclamped inductive waveform


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Figure 18. Switching time waveform

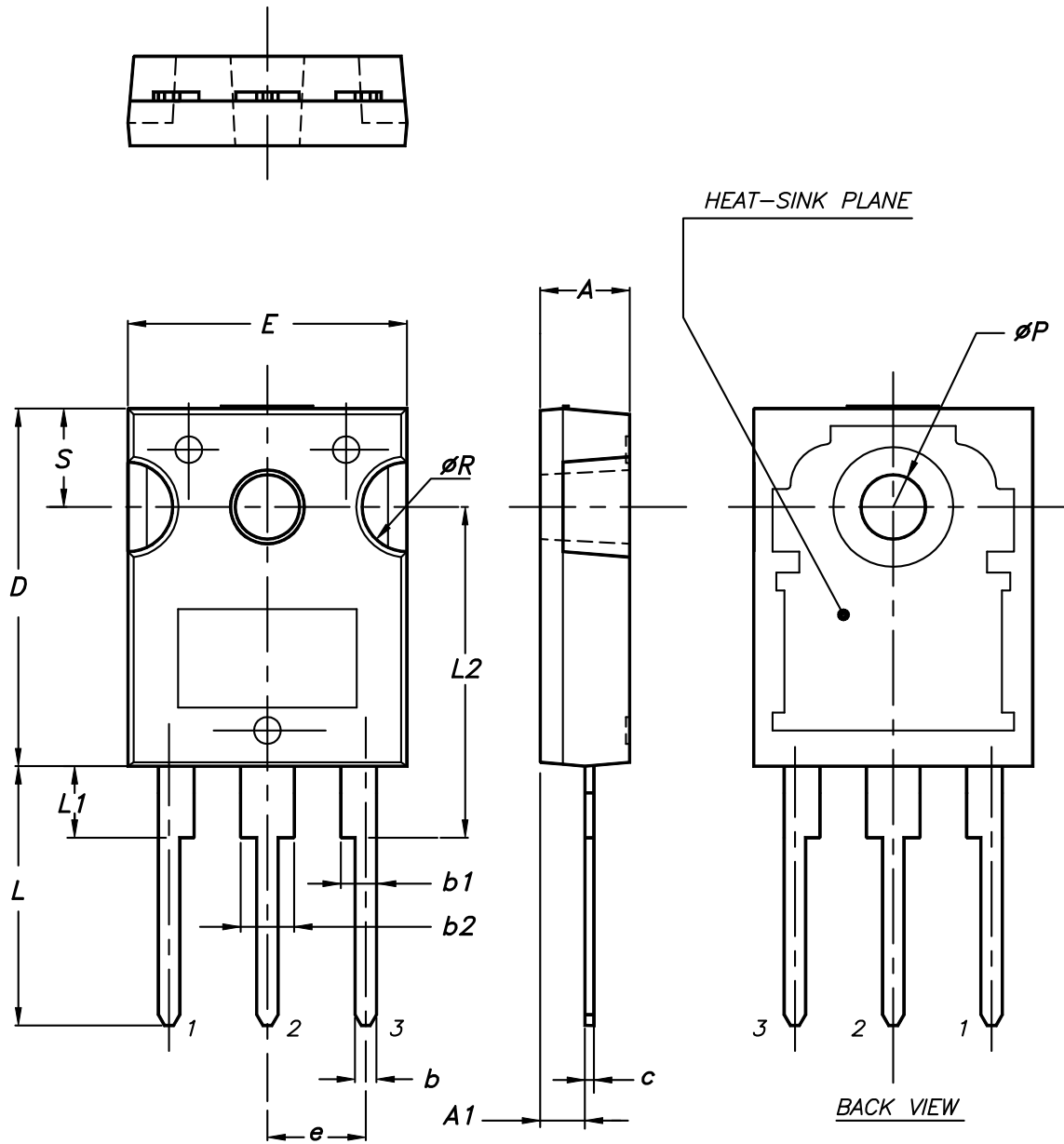

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4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK®** packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK® is an ST trademark.

4.1 TO-247 package information

Figure 19. TO-247 package outline



0075325_9

Table 8. TO-247 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.85		5.15
A1	2.20		2.60
b	1.0		1.40
b1	2.0		2.40
b2	3.0		3.40
c	0.40		0.80
D	19.85		20.15
E	15.45		15.75
e	5.30	5.45	5.60
L	14.20		14.80
L1	3.70		4.30
L2		18.50	
ØP	3.55		3.65
ØR	4.50		5.50
S	5.30	5.50	5.70

Revision history

Table 9. Document revision history

Date	Revision	Changes
27-Mar-2017	1	First release.
05-Nov-2018	2	<p>Removed maturity status indication from cover page. The document status is production data.</p> <p>Modified Table 1. Absolute maximum ratings, Table 5. Dynamic and Table 7. Source-drain diode</p> <p>Modified Figure 1. Safe operating area, Figure 3. Output characteristics, Figure 4. Transfer characteristics, Figure 5. Gate charge vs gate-source voltage, Figure 6. Static drain-source on-resistance, Figure 7. Capacitance variations, Figure 8. Normalized gate threshold vs. temperature, Figure 9. Normalized on-resistance vs. temperature, Figure 10. Normalized $V_{(BR)DSS}$ vs. temperature and Figure 12. Source-drain diode forward characteristics.</p> <p>Minor text changes.</p>

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